N-Channel Super Junction Power MOSFET Ⅳ

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

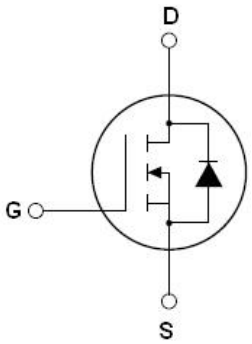
Features

- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant&Halogen Free

Application

- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）

$V_{DS\ min@Tjmax}$	650	V
$R_{DS(ON)TYP}$	180	mΩ
ID	18	A
Qg	22.8	nC



Schematic diagram

✧ **Intrinsic fast-recovery body diode**

Package Marking And Ordering Information

Device	Device Package	Marking
NCE60NF200T	TO-247	NCE60NF200T

TO-247

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (VGS=0V）	V_{DS}	600	V
Gate-Source Voltage (VDS=0V) AC (f>1 Hz)	V_{GS}	±30	V
Gate-Source Voltage (VDS=0V) DC	V_{GS}	±20	V
Continuous Drain Current at Tc=25°C	$I_{D\ (DC)}$	18	A
Continuous Drain Current at Tc=100°C	$I_{D\ (DC)}$	12.6	A
Pulsed drain current (Note 1)	$I_{DM\ (pluse)}$	54	A
Maximum Power Dissipation(Tc=25°C) Derate above 25°C	P_D	150 1.0	W W/°C
Avalanche current(Note 1)	I_{AS}	3.5	A
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50	V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+175	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	1.0	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	600			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=600V,V_{GS}=0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=600V,V_{GS}=0V			300	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±200	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	3.5	4.2	5.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=9A		180	200	mΩ
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		1157		pF
Output Capacitance	C_{oss}			60		pF
Reverse Transfer Capacitance	C_{rss}			1.5		pF
Total Gate Charge	Q_g	V_{DS}=400V,I_D=9A, V_{GS}=10V		22.8		nC
Gate-Source Charge	Q_{gs}			9.1		nC
Gate-Drain Charge	Q_{gd}			6		nC
Gate plateau voltage	Vgp			6.5		V
Intrinsic gate resistance	R_G	f = 1 MHz open drain		20		Ω
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=380V,I_D=9A, R_G=1.7Ω,V_{GS}=10V		25		nS
Turn-on Rise Time	t_r			16		nS
Turn-Off Delay Time	$t_{d(off)}$			75		nS
Turn-Off Fall Time	t_f			9		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			18	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				54	A
Forward On Voltage	V_{SD}	Tj=25°C,I_{SD}=18A,V_{GS}=0V		1.0	1.2	V
Reverse Recovery Time	t_{rr}	Tj=25°C,I_F=9A, di/dt=100A/μs		90		nS
Reverse Recovery Charge	Q_{rr}			0.32		uC
Peak Reverse Recovery Current	I_{rrm}			7		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. Tj=25℃,VDD=50V,VG=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

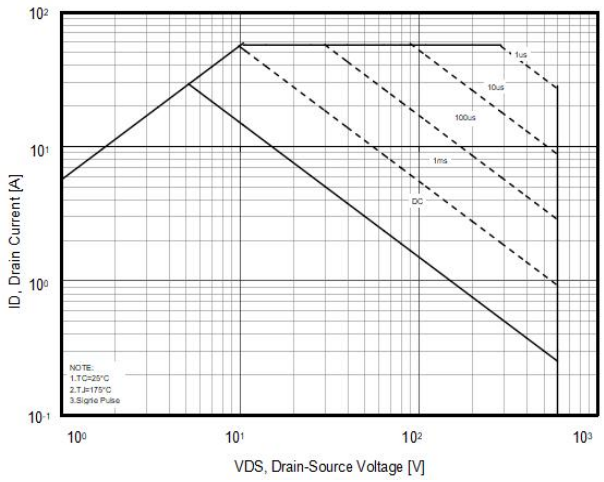


Figure2. Capacitance

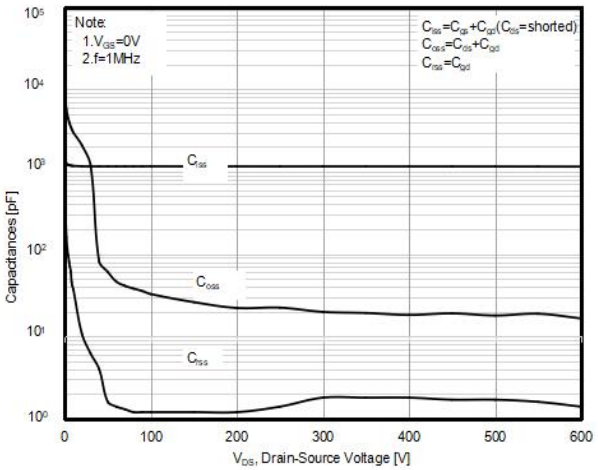


Figure3. Transfer characteristics

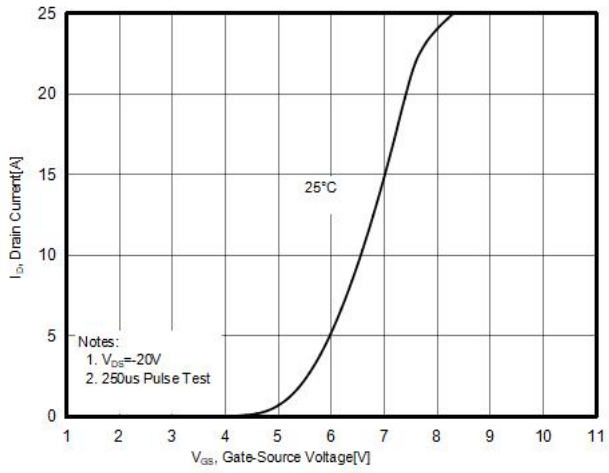


Figure4. Output characteristics

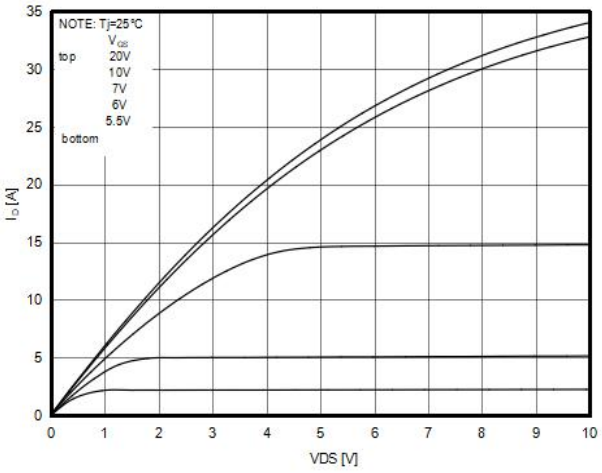


Figure5. $R_{DS(ON)}$ vs Junction Temperature

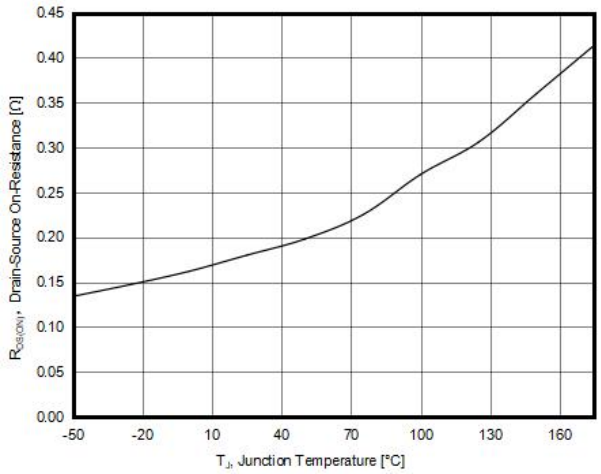


Figure6. BV_{DSS} vs Junction Temperature

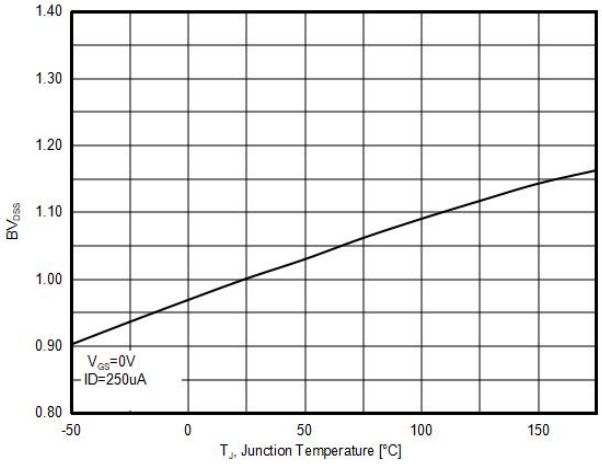


Figure7. Maximum I_D vs Junction Temperature

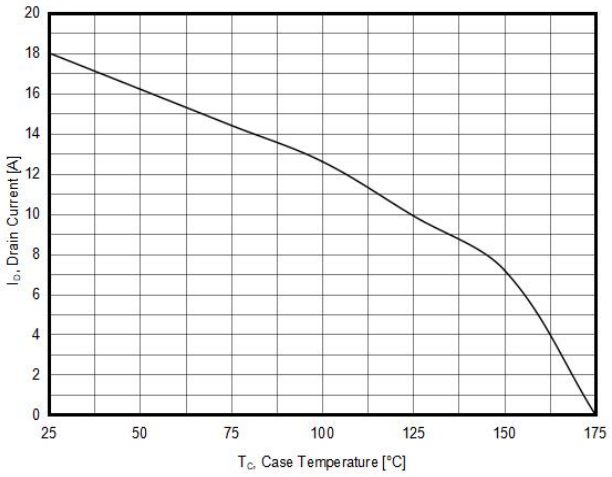


Figure8. Gate charge waveforms

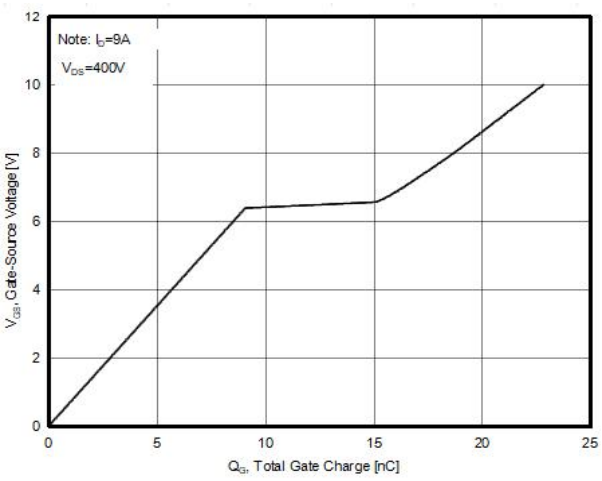


Figure9. Static drain-source on resistance

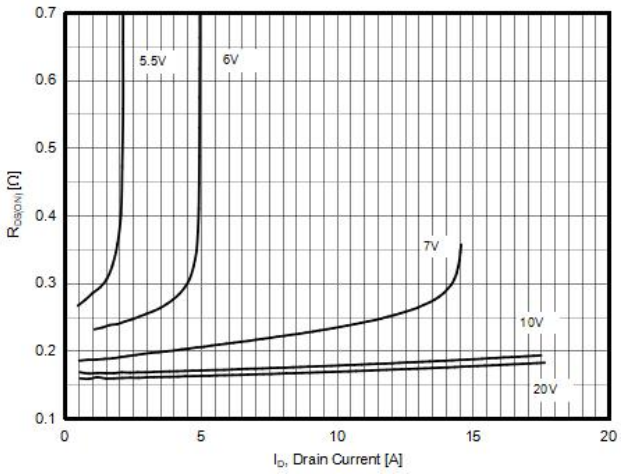
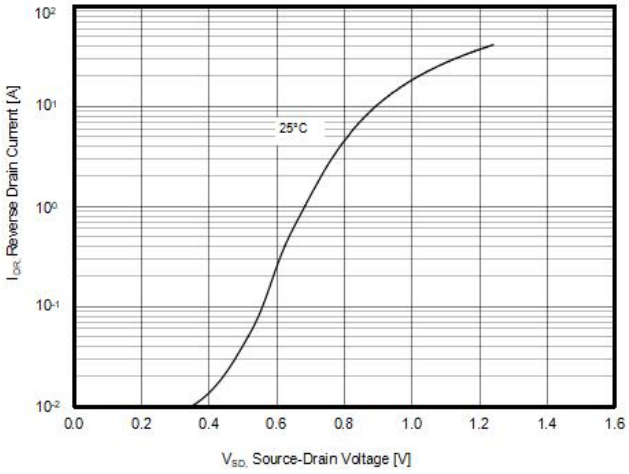
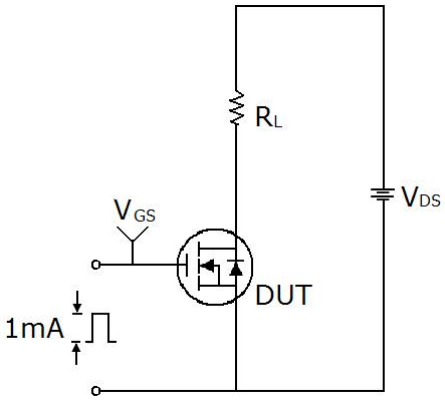


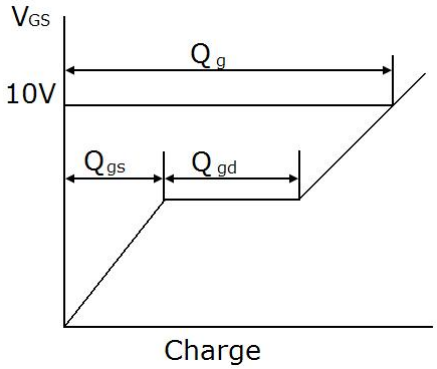
Figure10. Source-Drain Diode Forward Voltage



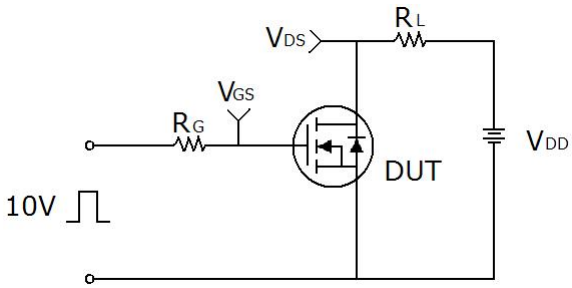
Test circuit

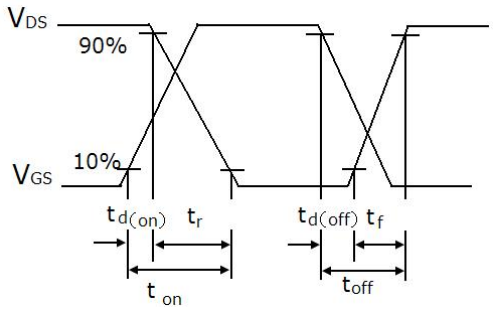
1）Gate charge test circuit & Waveform



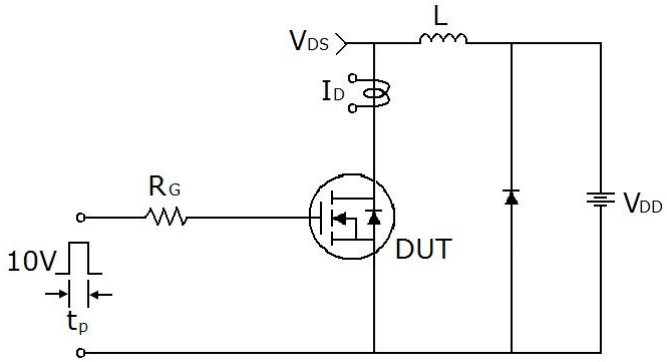


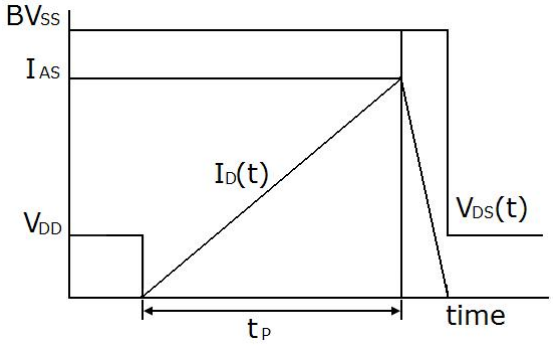
2）Switch Time Test Circuit：



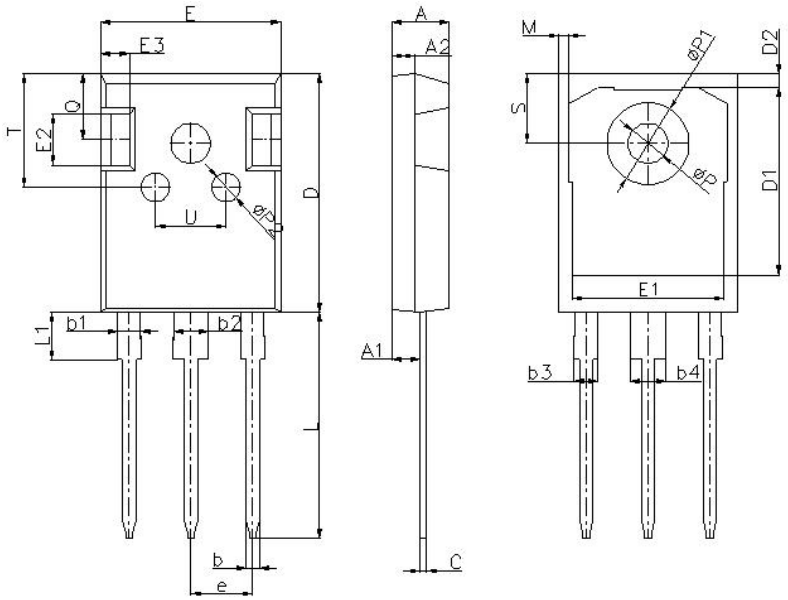


3）Unclamped Inductive Switching Test Circuit & Waveforms





TO-247-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	2.31	2.51	0.091	0.099
A2	1.90	2.10	0.075	0.083
b	1.16	1.26	0.046	0.050
b1	1.96	2.06	0.077	0.081
b2	2.96	3.06	0.117	0.120
b3	-	2.25	-	0.089
b4	-	3.25	-	0.128
C	0.59	0.66	0.023	0.026
D	20.90	21.10	0.823	0.831
D1	16.25	16.85	0.640	0.663
D2	1.05	1.35	0.041	0.053
E	15.70	15.90	0.618	0.626
E1	13.10	13.50	0.516	0.531
E2	4.40	4.60	0.173	0.181
E3	2.40	2.60	0.094	0.102
e	5.436BSC		0.214BSC	
L	19.80	20.10	0.780	0.791
L1	-	4.30	-	0.169
M	0.35	0.95	0.014	0.037
Q	5.60	6.00	0.220	0.236
S	6.05	6.25	0.238	0.246
T	9.80	10.20	0.386	0.402
U	6.00	6.40	0.236	0.252

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